Seat No.:	Enrolment No.
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GUJARAT TECHNOLOGICAL UNIVERSITY

BE - SEMESTER-V • EXAMINATION - SUMMER • 2014

Su	bject	Code: 152401 Date: 11-06-2014	
Su	bject	Name: Power Electronics Devices and Components	
	_	0.30 am - 01.00 pm Total Marks: 70	
	truction	_	
	1.	Attempt all questions.	
	2.	Make suitable assumptions wherever necessary.	
	3.	Figures to the right indicate full marks.	
	4.	Notations/ symbols used have usual meanings.	
Q.1	(a)	Discuss the following: (i) Building blocks of PES	08
	<i>a</i>	(ii) Concept of Power processing.	
	(b)	Explain the following diodes in brief: (i) PiN diode (ii) Schottky barrier diode	06
Q.2	(a)	Discuss losses in a power BJT.	07
	(b)	Why isolation is required in a power electronic system? Explain opto-coupler in detail.	07
		OR	
	(b)	Draw and explain UJT with an application circuit.	07
Q.3	(a)	Draw detailed V-I characteristics of the SCR and explain the term "Latching and Holding current".	08
	(b)	(i) Define: Commutation. Why it is needed?(ii) What are the requirements for the successful commutation?	06
		(iii) Which specification(s) is useful to design a commutation circuitry? OR	
Q.3	(a)	Draw and discuss turn-on mechanism for an SCR.	08
C	(b)	State various types of commutation. Discuss Class B commutation in detail.	06
Q.4	(a)	Compare: IGBT with Power MOSFET.	07
	(b)	With neat diagram discuss switching characteristic of Power MOSFET. OR	07
Q.4	(a)	What is IGBT? Derive the equivalent circuit of IGBT from its structural details.	07
	(b)	Compare: Converter grade thyristor with Inverter Grade thyristor.	07
Q.5	(a)	Write short note on: GTO.	07
	(b)	Discuss heat sink and cooling requirements with reference a power device. OR	07
Q.5	(a)	Write short note on: MCT.	07
.	(b)	Explain in brief: SIT, SITH.	07
